

Growth and applications of Group III-nitrides

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Characterization of Be-Implanted GaN Annealed at High Temperatures. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	1
2	GaN Growth by Remote Plasma MOCVD: Chemistry and Kinetics by Real Time Ellipsometry. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	0
3	Characterization of Be-Implanted GaN Annealed at High Temperatures. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 203-208.	1.0	1
4	GaN Growth by Remote Plasma MOCVD: Chemistry and Kinetics by Real Time Ellipsometry. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 173-178.	1.0	0
5	Characterisation of rhenium Schottky contacts on n-type Al _x Ga _{1-x} N. Electronics Letters, 1999, 35, 745.	0.5	20
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9	Comparison of N-face and Ga-face AlGa _N /GaN-Based High Electron Mobility Transistors Grown by Plasma-Induced Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1999, 38, 4962-4968.	0.8	28
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